

WHAT IS CLAIMED IS:

1. A wafer-like semiconductor sensor, comprising:
a wafer-like base formed of a plurality of layers of chemically-hardened glass, the wafer-like base defining a recessed pocket therein; and
an electronics module coupled to the recessed pocket of the wafer-like base and containing a sensor.
2. The wafer-like semiconductor sensor of claim 1, wherein the chemically-hardened glass provides a surface suitable vacuum chucking.
3. The wafer-like semiconductor sensor of claim 1, and further comprising a layer of material disposed between the plurality of layers of chemically-hardened glass.
4. The wafer-like semiconductor sensor of claim 3, wherein the layer of material includes an opaque coating.
5. The wafer-like semiconductor sensor of claim 3, wherein the layer of material includes an anti-shatter film.
6. The wafer-like semiconductor sensor of claim 1, wherein the chemically-hardened glass is formed of a material that provides reduced RF obstruction.
7. A wafer-like substrate, comprising:
an upper annular layer formed of chemically-hardened glass;
a lower layer formed of chemically-hardened glass; and
wherein the annular upper layer is chemically bonded to the lower layer.
8. The wafer-like substrate of claim 7, wherein the upper annular layer has an inner perimeter defining a region configured to seat an electronics module.
9. The wafer-like substrate of claim 7, wherein the upper annular layer has a thickness of .4 mm.
10. The wafer-like substrate of claim 7, wherein the lower layer has a thickness of .4 mm.
11. The wafer-like substrate of claim 7, and further comprising an opaque coating interposed between the upper annular layer and the lower layer.
12. The wafer-like substrate of claim 7, and further comprising an anti-shatter layer interposed between the upper annular layer and the lower layer.
13. The wafer-like substrate of claim 7, wherein an outer perimeter of the upper annular layer has a SEMI notch.
14. The wafer-like substrate of claim 7, wherein an outer perimeter of the lower layer has a SEMI notch.

15. The wafer-like substrate of claim 7, wherein the upper annular layer defines a recessed pocket having a thickness of 0.4mm.
16. The wafer-like substrate of claim 7, wherein the upper annular layer is chemically bonded to the lower layer with epoxy.
17. A method of making a wafer-like sensor, the method comprising:
 - providing a chemically-hardened base glass layer;
 - providing a chemically-hardened upper annular glass layer;
 - bonding the chemically-hardened base glass layer to the chemically-hardened annular glass layer to provide a chemically-hardened wafer-like substrate having a recessed pocket; and
 - mounting an electronics housing within the recessed pocket.
18. The method of claim 17, and further comprising applying an anti-shatter layer to at least one of the chemically-hardened base glass layer and the chemically-hardened annular glass layer.
19. The method of claim 17, and further comprising applying an opaque coating to at least one of the chemically-hardened base glass layer and the chemically-hardened annular glass layer.